ABSTRACT

A method of generating a mask design having optical proximity correction features disposed therein. The methods includes the steps of obtaining a desired target pattern having features to be imaged on a substrate; determining an interference map based on the target pattern, the interference map defining areas of constructive interference and areas of destructive interference between at least one of the features to be imaged and a field area adjacent the at least one feature; and placing assist features in the mask design based on the areas of constructive interference and the areas of destructive interference.